## ASSP for Image Processing

#### CMOS

A/D Converter (1-channel, 8-bit, 45MHz)

# **MB40C558**

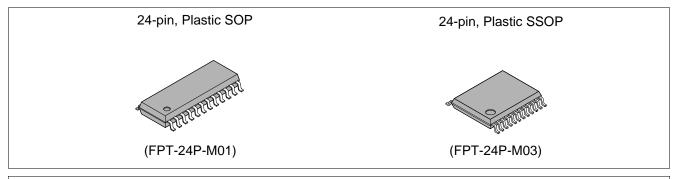
#### DESCRIPTION

The MB40C558 is a high-speed A/D converter using high-speed CMOS process technology.

#### ■ FEATURES

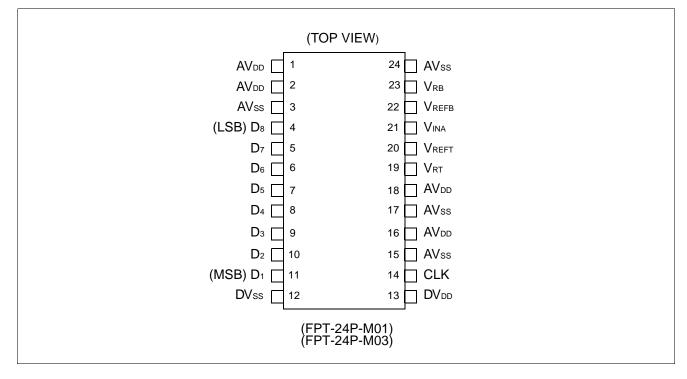
- Resolution: 8 bits
- Linearity error: ±0.20% (Typ.)
- Maximum conversion rate: 45 MSPS (Min.)
- Power supply voltage: Analog section +5.0 V
  - Digital section +3.0 V or +5.0 V
- Digital input voltage range: TTL level
- Digital output voltage range: CMOS level compatible
- Analog input voltage range: 0.5 to 3 V (with 2 Vp-p)
- Analog input capacity: 15 pF (Typ.)
- Power consumption: 110 mW (Typical: @fcLK = 45 MHz, AVDD = 5 V, DVDD = 3 V) 135 mW (Typical: @fcLK = 45 MHz, AVDD = 5 V, DVDD = 3 V)
- Additional function: Reference voltage generator circuit: VREFT = 3 V, VREFB = 1 V
- Package options: SOP24, SSOP24

#### PACKAGES



This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.





#### ■ PIN DESCRIPTION

Pin No.	Pin name	Functions
1, 2, 16, 18	AVdd	Analog power supply pins (+5 V)
13	DVdd	Digital power supply pin (+3 or +5 V)
3, 15, 17, 24	AVss	Analog power ground pins (0 V)
12	DVss	Digital power ground pin (0 V)
4 to 11	D <sub>1</sub> to D <sub>8</sub>	Digital output pins. D1: MSB, D8: LSB
14	CLK	Clock input pin
21	Vina	Analog input pin. Input range: VRB to VRT (2 Vp-p between 0.5 to 3 V)
19	Vrt	Reference voltage input pin (3 V)
20	Vreft	Reference voltage output pin. When connected to $V_{RT}$ , the pin generates $0.6 \times AV_{DD}$ (3 V).
23	Vrb	Reference voltage input pin (1 V)
22	Vrefb	Reference voltage output pin. When connected to $V_{\text{RB}}$ , the pin generates $0.2 \times AV_{\text{DD}}$ (1 V).

Values within () are typical values.

#### NOTES ON USE

- Be sure to bypass the AV<sub>DD</sub>, DV<sub>DD</sub>, V<sub>RT</sub> and V<sub>RB</sub> pins to the ground using a high-frequency capacitor. The high-frequency capacitor should be connected as near the pin as possible.
- Provide four clocks or more immediately after the power up to prevent current dissipation due to the indeterminate internal logic.

#### ■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Rat	Unit	
	Symbol	Min.	Max.	Unit
Power supply voltage	AVdd, DVdd	-0.3	7.0	V
Input voltage	CLK, Vina Vrt, Vrb	-0.3	AVDD+0.3	V
Output voltage	D <sub>1</sub> to D <sub>8</sub>	-0.3	DV <sub>DD</sub> +0.3	V
Storage temperature	Tstg	-55	+125	°C

**WARNING:** Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

#### RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Value			
Farameter	Symbol	Min.	Тур.	Max.	Unit	
Analog input voltage	VINA	Vrb	_	Vrt	V	
Analog reference voltage: T	Vrt	-	-	3.00	V	
Analog reference voltage: B	Vrb	0.50	-	-	V	
Analog reference voltage range	Vrt–Vrb	1.90	2.00	2.10	V	
Digital "H" level input voltage	VIHD	2.4	_	_	V	
Digital "L" level input voltage	Vild	-	-	0.8	V	
Digital input current	lid	-	-	5	μA	
Clock frequency	fclк	0.1	-	45	MHz	
Minimum "H" level clock pulse width	tw+	10.0	-	-	ns	
Minimum "L" level clock pulse width	tw-	10.0	_	-	ns	
Operating temperature range	Та	-20	-	70	°C	

**WARNING:** Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

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#### • When using a single power supply

Parameter	Symbol		Unit		
Faraneter	Symbol	Min.	Тур.	Max.	Onic
Power supply voltage	AVdd, DVdd	4.75	5.00	5.25	V

#### • When using dual power supplies

Parameter	Symbol		Unit		
Faranieter	Symbol	Min.	Тур.	Max.	Onit
Power supply voltage	AVdd	4.75	5.00	5.25	V
	DVdd	2.70	3.00	3.30	V

**WARNING:** Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

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### ■ ELECTRICAL CHARACTERISTICS (Using a Single Power Supply)

#### **DC Characteristics**

(1) Analog section

		(AV	'DD = DVDD = 4.	75 V to +5.25 V	∕, Ta = −20°C t	to +70°C)
Parameter	Symbol		Value		Unit	
Farameter		Symbol	Min.	Тур.	Max.	Onit
Resolution		-	-	8	-	bit
Linearity error	DC precision	LE	-	±0.20	±0.30	%
Differential linearity error	DC precision	DLE	-	±0.12	±0.20	%
Analog input capacity		CINA	-	15	_	pF
Reference voltage: T		Vreft	-	$0.6  imes AV_{DD}$	_	V
Reference voltage: B		Vrefb	-	$0.2 \times AV_{DD}$	_	V
Reference current		IRB	-16.0	-8.0	-2.0	mA
Analog power supply current		Aldd	-	18.0	31.0	mA
Digital power supply current		DIDD	_	9.0	15.0	mA

#### (2) Digital section

Parameter	Symbol		Unit		
Faranieter	Symbol	Min.	Тур.	Max.	Unit
Digital "H" level output voltage	Vонd	4.2	_	DVdd	V
Digital "L" level output voltage	Vold	-	-	0.4	V
Digital "H" level output current	Іон	-400	-	-	μA
Digital "L" level output current	Iol	_	Ι	1.6	mA

#### (3) Switching section

 $(AV_{DD} = DV_{DD} = 4.75 \text{ V to } +5.25 \text{ V}, \text{ Ta} = -20^{\circ}\text{C to } +70^{\circ}\text{C})$ 

Parameter	Symbol		Unit			
Farameter	Symbol	Min.	Тур.	Max.	Onic	
Maximum conversion rate	fs	45	_	_	MSPS	
Digital output delay time	tpd	0	5	14	ns	

#### ■ ELECTRICAL CHARACTERISTICS (Using Dual Power Supplies)

#### **DC Characteristics**

(1) Analog section

$(AV_{DD} = 4.7)$	75 V to +5.2	5 V, DV <sub>DD</sub> = 2.70 V to +	∙3.30 V Ta = −20°C	to +70°C)

Parameter		Symbol		Value	Unit	
Farameter		Symbol	Min.	Тур.	Max.	Unit
Resolution		-	-	8	-	bit
Linearity error	DC precision	LE	-	±0.20	±0.30	%
Differential linearity error	DC precision	DLE	-	±0.12	±0.20	%
Analog input capacity		CINA	-	15	_	pF
Reference voltage: T		Vreft	-	$0.6  imes AV_{DD}$	_	V
Reference voltage: B		Vrefb	-	$0.2 \times AV_{DD}$	_	V
Reference current		Irb	-16.0	-8.0	-2.0	mA
Analog power supply current		Aldd	-	18.0	31.0	mA
Digital power supply current		DIDD	_	6.0	10.0	mA

#### (2) Digital section

```
(AV_{DD} = 4.75 \text{ V to } +5.25 \text{ V}, \text{DV}_{DD} = 2.70 \text{ V to } +3.30 \text{ V Ta} = -20^{\circ}\text{C to } +70^{\circ}\text{C})
```

Parameter	Symbol		Unit		
Faranieter	Symbol	Min.	Тур.	Max.	Unit
Digital "H" level output voltage	Vohd	2.4	_	DVdd	V
Digital "L" level output voltage	Vold	-	-	0.4	V
Digital "H" level output current	Юн	-400	-	-	μA
Digital "L" level output current	lol	_	-	1.6	mA

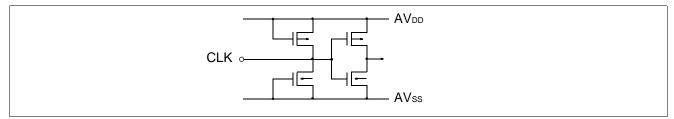
#### (3) Switching section

(AV<sub>DD</sub> = 4.75 V to +5.25 V, DV<sub>DD</sub> = 2.70 V to +3.30 V Ta = -20°C to +70°C)

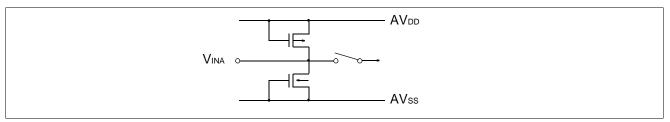
Parameter	Symbol	Value			Unit
		Min.	Тур.	Max.	Onic
Maximum conversion rate	fs	45	-	-	MSPS
Digital output delay time	tpd	0	6	15	ns

#### ■ EQUIVALENT CIRCUIT

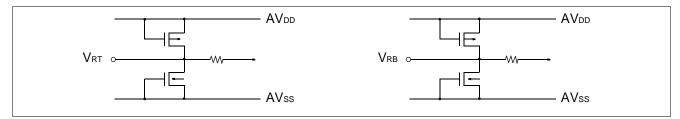
#### Clock input



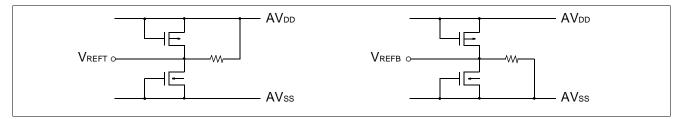
### Analog input



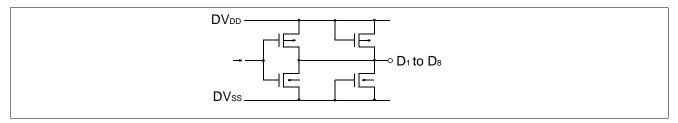
#### • Reference voltage input



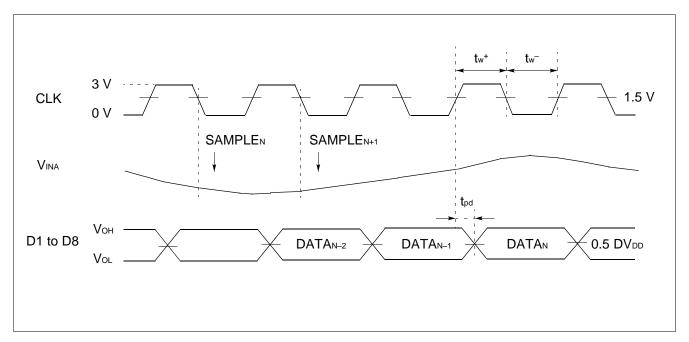
#### • Reference voltage output



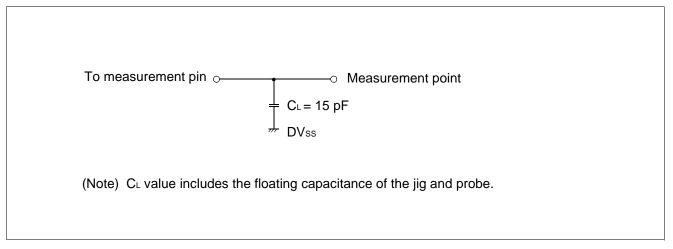
#### • Digital output



■ TIMING CHART



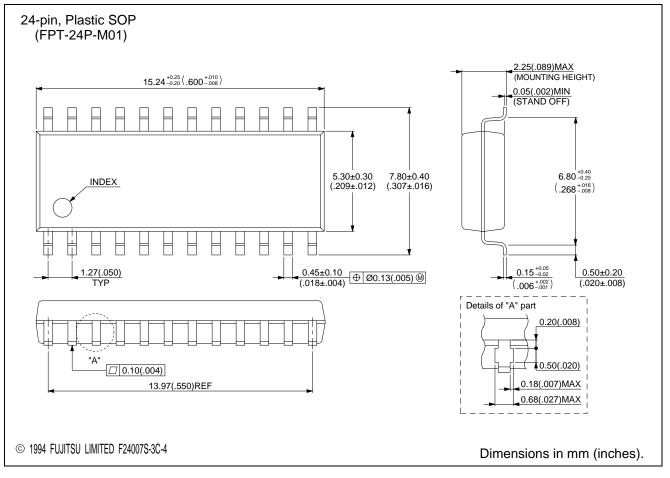
#### ■ DIGITAL OUTPUT BUFFER LOAD CIRCUIT



#### ■ ORDERING INFORMATION

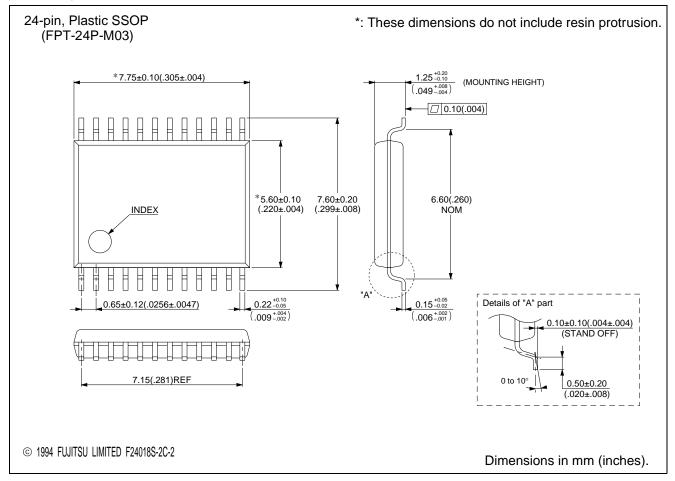
Part number	Package	Remarks
MB40C558PF	24-pin, Plastic SOP (FPT-24P-M01)	
MB40C558PFV	24-pin, Plastic SSOP (FPT-24P-M03)	

#### ■ PACKAGE DIMENSIONS



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# FUJITSU LIMITED

For further information please contact:

#### Japan

FUJITSU LIMITED **Corporate Global Business Support Division Electronic Devices** KAWASAKI PLANT, 4-1-1, Kamikodanaka Nakahara-ku, Kawasaki-shi Kanagawa 211-88, Japan Tel: (044) 754-3763 Fax: (044) 754-3329

#### North and South America

FUJITSU MICROELECTRONICS, INC. Semiconductor Division 3545 North First Street San Jose, CA 95134-1804, U.S.A. Tel: (408) 922-9000 Fax: (408) 432-9044/9045

#### Europe

FUJITSU MIKROELEKTRONIK GmbH Am Siebenstein 6-10 63303 Dreieich-Buchschlag Germany Tel: (06103) 690-0 Fax: (06103) 690-122

#### Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE. LIMITED #05-08, 151 Lorong Chuan New Tech Park Singapore 556741 Tel: (65) 281-0770 Fax: (65) 281-0220

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